

-	San Jose, CA 96	6138				
	PRODUCT/PR	ROCESS C	HANGE NO	TICE (PCN)		
PCN #: W150	•	pril 13, 2015	MEANS OF DISTIN  ☐ Product Mark	NGUISHING CHANGED DEVICES:		
Product Affected	: 74CBTLV3244QG, 74CBTLV 74CBTLV3244PGG, 74CBTL		☐ Back Mark			
	/4CB1Lv3244PGG, /4CB1L	V 3244PUU0	■ Date Code	Prefix SA5 before datecode		
			□ Other	Tienx SAS before datecode		
Date Effective:	July 13, 2015		- Other			
Contact:	IDT PCN DESK		Attachment:	Yes No		
E-mail:	pcndesk@idt.com		Samples: Available	e upon request		
DESCRIPTION	AND PURPOSE OF CHANGE:					
☐ Die Technolog	gy					
☐ Wafer Fabrica	ation Process					
☐ Assembly Process  This notification is to advise our customer the above part numbers water fab product						
Equipment Equipment Semiconductor Manufacturin				IDT Hillsboro, Oregon (Fab 4) to Taiwan		
☐ Material	Someonad	ctor ivianaractarin	g corporation (15)	·)·		
Testing  There is no expected change to the data sheet, package or backend manufacturing process.						
■ Manufacturing	g Site	.1		oi an Ann ann aile		
□ Data Sheet	There is no	change to orderin	g part number and dev	vice top mark.		
□ Other						
	QUALIFICATION SUMMARY:					
Based on wafer a reliability of the	and component level qualification a	nd characterizatio	on tests, there is no cha	ange to the performance or		
*	•					
	CKNOWLEDGMENT OF RECE					
IDT records indicate that you require written notification of this change. Please use the acknowledgement below or E-Mail						
	l or request additional information.	If IDT does not re	ccive acknowledgeme	ent within 30 days of this notice		
	ed that this change is acceptable.					
	right to ship either version manufac	ctured after the pr	ocess change effective	e date until the inventory		
on the earlier ver	rsion has been depleted.					
Customer:			Approval for ship	ments prior to effective date.		
Name/Date:		F-	Mail Address:			
Tumo, Date.		L				
Title:		Ph	one# /Fax# :			
CUSTOMER C	OMMENTS:					
IDT ACKNOW	LEDGMENT OF RECEIPT:					
RECD. BY:			DATE:			



Integrated Device Technology, Inc. 6024 Silver Creek Valley Road San Jose, CA 96138

# PRODUCT/PROCESS CHANGE NOTICE (PCN)

#### ATTACHMENT I - PCN #: W1503-02

**PCN Type:** Wafer Fab Manufacturing Site Change - IDT Fab 4 to TSMC

**Data Sheet Change:** No

## **Detail Of Change:**

This notification is to advise our customers that IDT has successfully completed the transfer of the above part numbers wafer fab production from IDT Hillsboro, Oregon (Fab 4) to Taiwan Semiconductor Manufacturing Corporation (TSMC).

TSMC has closely matched the IDT Fab 4 process for this transferred part, using the same design rules of the existing product.

There is no expected change to the data sheet, package or backend manufacturing process. Characterization data of material manufactured at TSMC is comparable to material manufactured at IDT Fab 4, Hillsboro.

There is no change to ordering part number and device top mark.

Please contact your local IDT sales representative to request samples or additional information.



# **TSMC Transfer Qualification Test Result Summary**

Technology Information: 0.5 μm, 3.3 V Fab Location: TSMC Fab 3

### Technology Qualification Vehicle Test Summary – JESD47 Recommended Tests

Test / Conditions	Logic Vehicle: 40V024SA5  Sample Size/ Rejects/ each lot
High Temperature Operating Life (Dynamic) JESD22-A108B, +125°C @ 1000 hours or equivalent	79 / 0
Temperature Cycle JESD22-A104B, -55°C -/125°C, 1000 cycles	45 / 0
High Temperature Storage Bake JESD22-A-103-B, 150°C, 1000 hrs	77 / 0
ESD: Human Body Model JESD22-A114F, Rating: 2000V	3/0
ESD: Charged Device Model JEDEC 22-101C, Rating: 500V	3/0
ESD: Machine Model JESD22-A115B, Rating: 200V	3/0
Latch-up JESD78B	6/0
Electrical Characterization per Datasheet conditions	10

#### Technology Qualification Vehicle Test Summary – Supplemental Tests

Test / Conditions	Logic Vehicle: 40V024SA5
Test / Conditions	Sample Size/ Rejects/ each lot
Ball Shear Test JESD22-B116-A, Ball Shear Strength > 5.7g	5 / 0
Highly Accelerated Stress Test (HAST) EIA/JESD22-A110B, 130°C/85%R.H. Vcc max for 100 hours.	45 / 0
Autoclave EIA/JESD22-A102C, 168hrs @ 2 ATM, Saturated Steam @ 121°C	45 / 0

 $Note: For\ HAST,\ Autoclave\ and\ Temperature\ Cycle,\ samples\ have\ been\ subjected\ to\ pre-conditioning\ per\ JESD22-A113$